



DUAL P-CHANNEL 60V ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} Max	I _D T _A = +25°C
-60V	$55m\Omega$ @ V_{GS} = -10 V	-4.8A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Disconnect Switches
- Motor Drive

Features

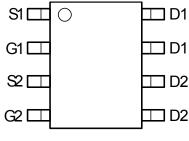
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Profile SOIC Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

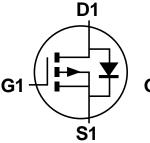
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.074 grams (Approximate)







Top View





D2

Equivalent Circuit

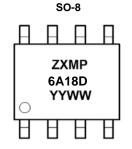
Ordering Information (Notes 4 & 5)

Product	Compliance	Case	Quantity per reel
ZXMP6A18DN8TA	Standard	SO-8	500
ZXMP6A18DN8TC	Standard	SO-8	2,500
ZXMP6A18DN8QTC	Automotive	SO-8	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMP6A18D = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 11 = 2011) WW = Week (01 - 53)



Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-60	V
Gate-Source Voltage		V _{GS}	±20	V
	(Notes 7 & 9)		-4.8	
Continuous Drain Current (V _{GS} = 10V)	T _A = +70°C (Notes 7 & 9)	I _D	-3.8	А
	(Notes 6 & 9)		-3.7	
Pulsed Drain Current	(Notes 8)	I _{DM}	-23	Α
Continuous Source Current (Body Diode)	(Notes 7)	Is	-3.3	Α
Pulsed Source Current (Body Diode)	(Notes 8)	I _{SM}	-23	Α
Single Pulsed Avalanche Energy (L = 0.1mH)	(Note 11)	E _{AS}	38.2	mJ
Single Pulsed Avalanche Current (L = 0.1mH)	(Note 11)	I _{AS}	27.6	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

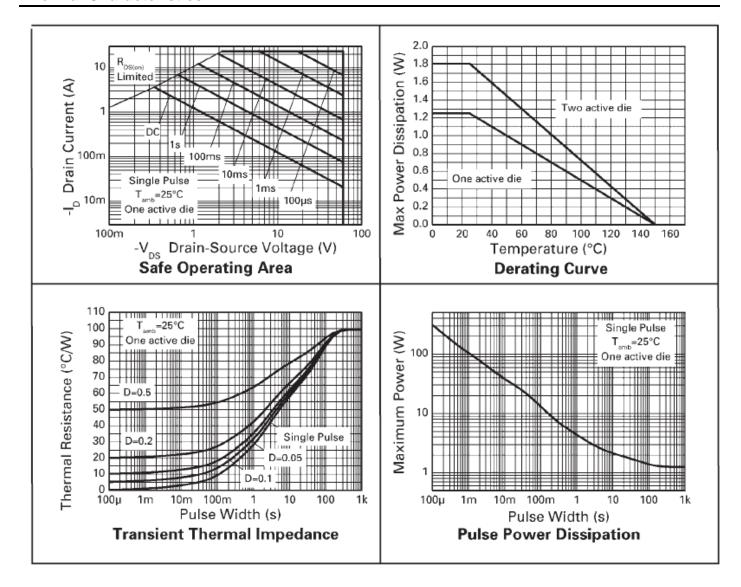
Characteristic		Symbol	Value	Unit	
	(Notes 6 & 9)		1.25 10		
Power Dissipation Linear Derating Factor	(Notes 6 & 10)	P _D	1.8 14	W mW/°C	
	(Notes 7 & 9)		2.1 17		
	(Notes 6 & 9)		+100	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 7 & 10)	$R_{ hetaJA}$	+69		
	(Notes 7 & 9)		+58		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Notes:

- 6. For a dual device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 1oz copper in still air conditions.
- 7. For a dual device surface mounted FR4 PCB measured at $t \leq 10 \mbox{ sec.}$
- 8. Repetitive rating 25mm x 25mm x 1.6mm FR4 PCB, D = 0.02, pulse width = 300µs pulse width limited by maximum junction temperature.
- 9. For a dual device with one active die.
- 10. For a device with two active die running at equal power.
- 11. IAR and EAR rating are based on low frequency and duty cycles to keep T_J = +25°C.



Thermal Characteristics





Electrical Characteristics (@T_A= +25°C, unless otherwise specified.)

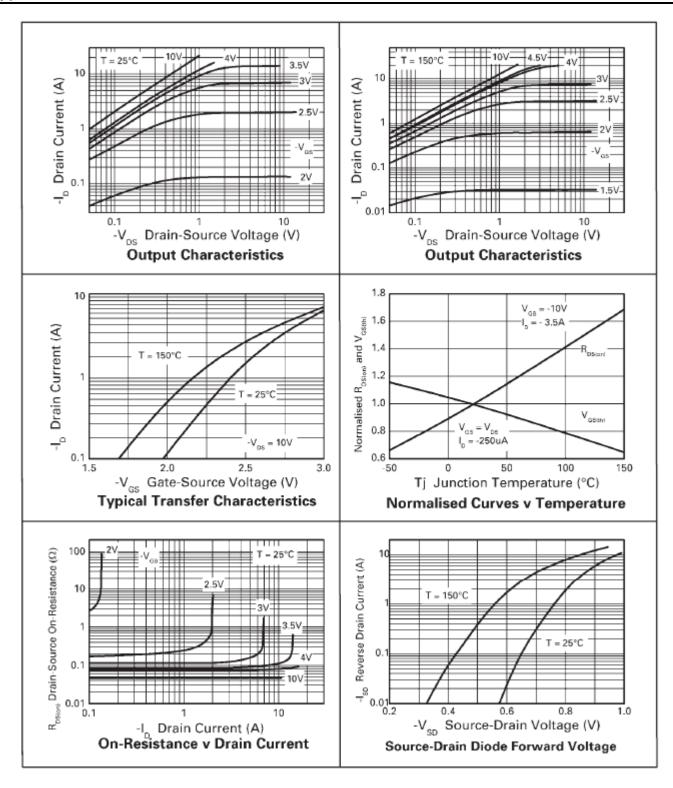
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	I _D = -250μA, V _{GS} = 0V	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	1
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	/
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1	_	_	V	$I_D = -250 \mu A, V_{DS} = V_0$	GS
Static Prain Source On Registance (Note 12)	0			0.055	Ω	$V_{GS} = -10V, I_D = -3.5A$	4
Static Drain-Source On-Resistance (Note 12)	R _{DS(ON)}	_	_	0.08	12	V _{GS} = -4.5V, I _D = -2.9	Α
Forward Transconductance (Notes 12 & 14)	g _{fs}	_	8.7	_	S	V _{DS} = -15V, I _D = -3.5A	4
Diode Forward Voltage (Note 12)	V _{SD}	_	-0.85	-0.95	V	I _S = -4.2A, V _{GS} = 0V,	T _J = +25°C
Reverse Recovery Time (Note 14)	t _{rr}		37	_	ns	I _F = -2.1A, di/dt = 100A/μs, T _J = +25°C	
Reverse Recovery Charge (Note 14)	Q _{rr}	_	56	_	nC		
DYNAMIC CHARACTERISTICS (Note 14)							
Input Capacitance	C _{iss}		1580	_	pF	.,	
Output Capacitance	Coss	_	160	_	pF	$V_{DS} = -30V, V_{GS} = 0V$ f = 1MHz	′
Reverse Transfer Capacitance	C _{rss}	_	140	_	pF	1 - 1101112	
Total Gate Charge (Note 13)	Qg	_	23	_	nC	V _{GS} = -5V	
Total Gate Charge (Note 13)	Qg	_	44	_	nC	V _{DS} = -30V	$V_{DS} = -30V$
Gate-Source Charge (Note 13)	Q _{gs}	_	3.9	_	nC	V _{GS} = -10V	$I_D = -3.5A$
Gate-Drain Charge (Note 13)	Q _{gd}	_	9.8	_	nC	1	
Turn-On Delay Time (Note 13)	t _{D(on)}	_	4.6	_	ns	V_{DD} = -30V, V_{GS} = -10V I_D = -1A, $R_G \approx 6.0\Omega$	
Turn-On Rise Time (Note 13)	t _r	_	5.8	_	ns		
Turn-Off Delay Time (Note 13)	t _{D(off)}	_	55	_	ns		
Turn-Off Fall Time (Note 13)	t _f	_	23	_	ns		

Notes:

- 12. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%.
 13. Switching characteristics are independent of operating junction temperatures.
 14. For design aid only, not subject to production testing.

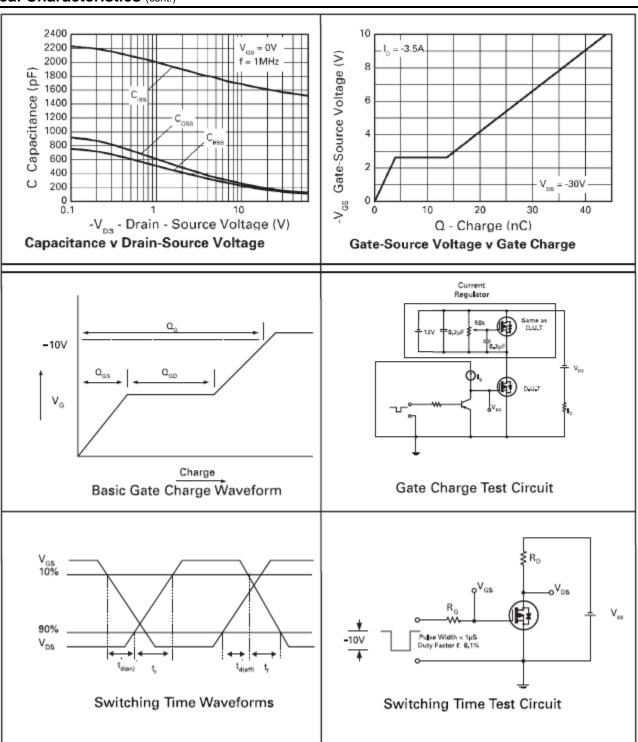


Typical Characteristics





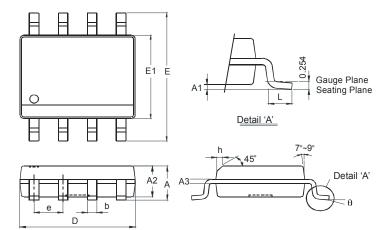
Typical Characteristics (cont.)





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

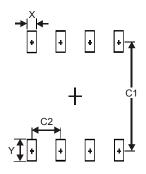


SO-8						
Dim	Min	Max				
Α	-	1.75				
A1	0.10	0.20				
A2	1.30	1.50				
А3	0.15	0.25				
b	0.3	0.5				
D	4.85	4.95				
Е	5.90	6.10				
E1	3.85 3.95					
е	e 1.27 Typ					
h	-	0.35				
L	0.62	0.82				
θ	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.





Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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